

HIGH DENSITY MOUNTING PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS

APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- VDE 0884 in 3 available lead form : -
- STD
- G form
- SMD approved to CECC 00802
- Certified to EN60950 by the following
Test Bodies :-
Nemko - Certificate No. P96102022
Fimko - Registration No. 192313-01..25
Semko - Reference No. 9639052 01
Demko - Reference No. 305969

DESCRIPTION

The ISP817, ISP827, ISP847 series of optically coupled isolators consist of infrared light emitting diodes and NPN silicon photo transistors in space efficient dual in line plastic packages.

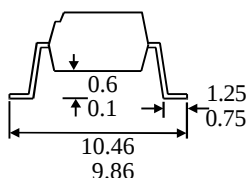
FEATURES

- Options :-
10mm lead spread - add G after part no.
Surface mount - add SM after part no.
Tape&reel - add SMT&R after part no.
- High Current Transfer Ratio (50% min)
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- High BV_{CEO} (35Vmin)
- All electrical parameters 100% tested
- Custom electrical selections available

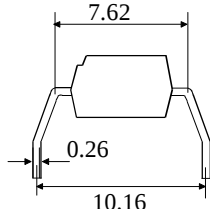
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

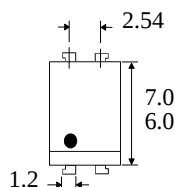
**OPTION SM
SURFACE MOUNT**



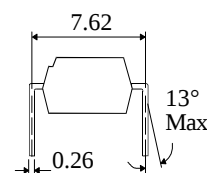
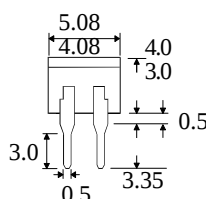
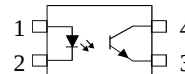
OPTION G



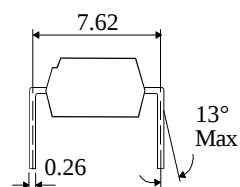
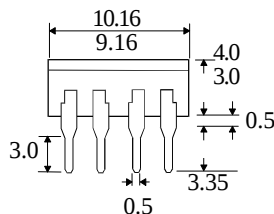
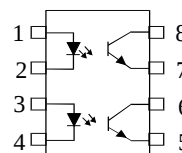
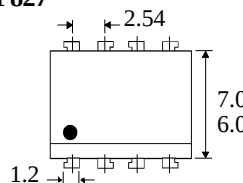
ISP817X ISP817



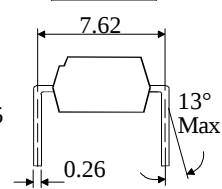
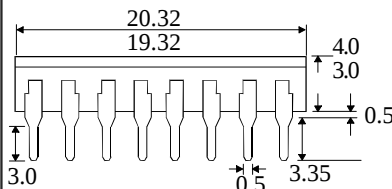
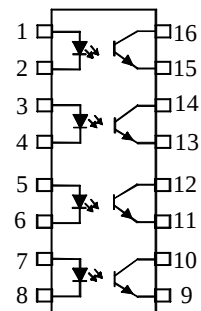
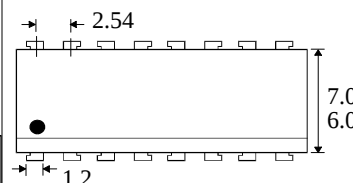
Dimensions in mm



ISP827X ISP827



ISP847X ISP847



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ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	_____	-55°C to + 125°C
Operating Temperature	_____	-55°C to + 100°C
Lead Soldering Temperature	(1/16 inch (1.6mm) from case for 10 secs) 260°C	

INPUT DIODE

Forward Current	_____	50mA
Reverse Voltage	_____	6V
Power Dissipation	_____	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO}	_____	35V
Emitter-collector Voltage BV_{ECO}	_____	6V
Power Dissipation	_____	150mW

POWER DISSIPATION

Total Power Dissipation	_____	200mW
(derate linearly 2.67mW/°C above 25°C)		

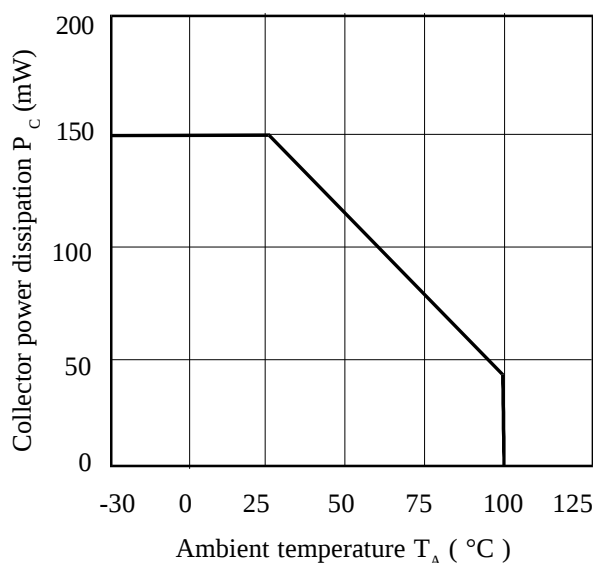
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)	6	1.2	1.4	V	$I_F = 20\text{mA}$ $I_R = 10\mu\text{A}$ $V_R = 6\text{V}$
	Reverse Voltage (V_R)				V	
	Reverse Current (I_R)			10	μA	
Output	Collector-emitter Breakdown (BV_{CEO}) (Note 2)	35			V	$I_C = 1\text{mA}$
	Emitter-collector Breakdown (BV_{ECO})	6			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current (I_{CEO})			100	nA	$V_{CE} = 20\text{V}$
Coupled	Current Transfer Ratio (CTR) (Note 2) ISP817, ISP827, ISP847	50		600	%	5mA I_F , 5V V_{CE}
	ISP817GB, ISP827GB, ISP847GB	100		600	%	5mA I_F , 5V V_{CE}
	ISP817BL, ISP827BL, ISP847BL	200		600	%	5mA I_F , 5V V_{CE}
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.2	V	20mA I_F , 1mA I_C
	Input to Output Isolation Voltage V_{ISO}	5300 7500			V_{RMS} V_{PK}	See note 1 See note 1
	Input-output Isolation Resistance R_{ISO}	5×10^{10}			Ω	$V_{IO} = 500\text{V}$ (note 1)
	Output Rise Time t_r		4	18	μs	$V_{CE} = 2\text{V}$,
	Output Fall Time t_f		3	18	μs	$I_C = 2\text{mA}$, $R_L = 100\Omega$

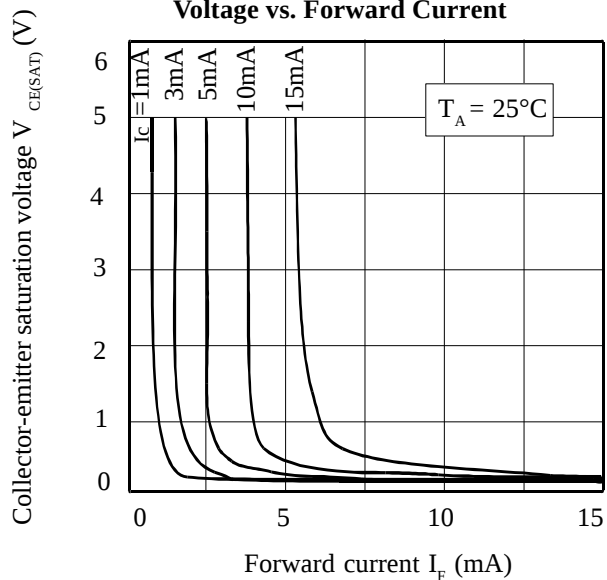
Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

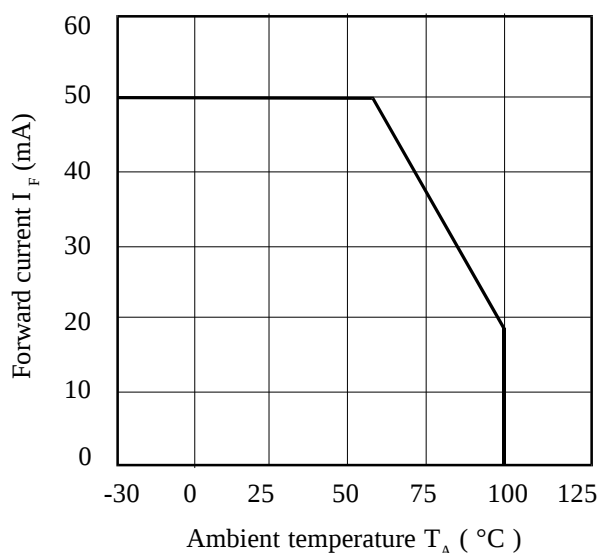
Collector Power Dissipation vs. Ambient Temperature



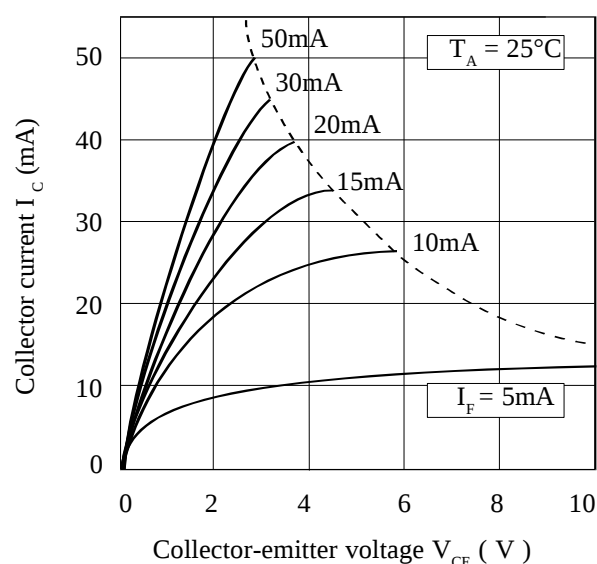
Collector-emitter Saturation Voltage vs. Forward Current



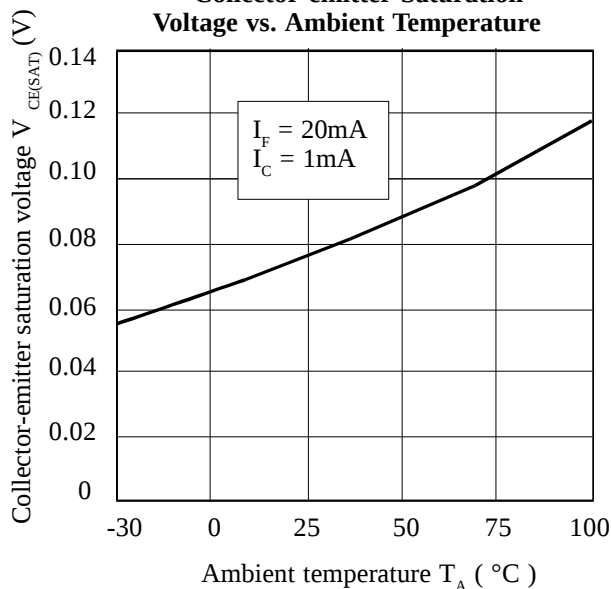
Forward Current vs. Ambient Temperature



Collector Current vs. Collector-emitter Voltage



Collector-emitter Saturation Voltage vs. Ambient Temperature



Current Transfer Ratio vs. Forward Current

